

LISTING OF THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

[Claims 1-29 (Cancelled)]

Claim 30 (Currently amended) A field effect transistor comprising:

a semiconductor substrate of a single crystal semiconducting material;

two spaced apart metal semiconductor compound regions forming a source and drain and defining a channel there between,

a first dielectric layer on said source and drain adjacent said channel,

a gate dielectric layer of local reacted metal of said metal used in said metal-semiconductor compound regions on said channel, and

a conductive layer on said gate dielectric to form a gate.

[Claims 31-32 (Cancelled)]

Claim 33 (Original) The field effect transistor of claim 30 wherein said gate dielectric layer includes TiO_2 .

[Claims 34-64 (Cancelled)]
